CRSZ015N08N4Z

SkyMOS4 N-MOSFET 80V, 1.1mΩ, 310A

Features

- Uses CRM(CQ) advanced SkyMOS4 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent Q_gx$R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

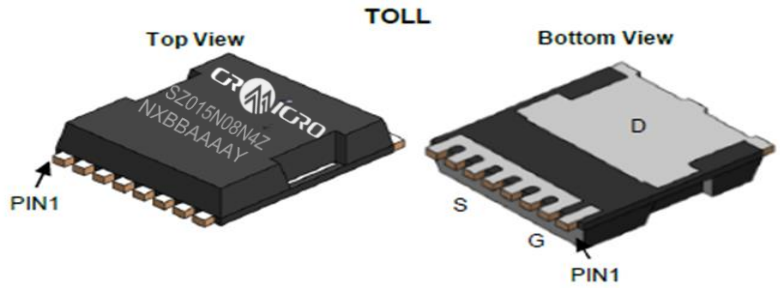
Product Summary

V_{DS}	80V
$R_{DS(on).typ}$	1.1mΩ
I_D	310A

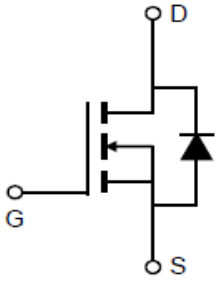
100% DVDS Tested
100% Avalanche Tested

Applications

- Motor control and drive
- Battery management System
- UPS (Uninterrupible Power Supplies)



CRSZ015N08N4Z



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRSZ015N08N4Z	SZ015N08N4Z	TOLL	Tape&Reel	N/A	N/A	2000pcs

Absolute Maximum Ratings

Parameter	**Symbol**	**Value**	**Unit**
Drain-source voltage	V_{DS}	80	V
Continuous drain current T_C = 25°C (Silicon limit) T_C = 25°C (Package limit) T_C = 100°C (Silicon limit)	I_D	 310 310 196	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	1240	A
Avalanche energy, single pulse (I_D = 88A, Rg=25Ω)[1]	E_{AS}	1921	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation (T_C = 25°C)	P_{tot}	237	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C

※. Notes:
1.EAS is tested at starting Tj = 25℃, L = 0.5mH, IAS =88A, VGS = 10V.
2.Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.

©China Resources Microelectronics (Chongqing) Limited

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.5	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	66	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	85	-	-	V	V_{GS}=0V, I_D=250μA
		85	-	-	V	V_{GS}=0V, I_D=1mA
Gate threshold voltage	$V_{GS(th)}$	2.2	3.0	3.8	V	V_{DS}=V_{GS},I_D=250μA
Zero gate voltage drain current	I_{DSS}	- -	- -	1 100	μA	V_{DS}=80V,V_{GS}=0V T_j=25°C T_j=125°C
Gate-source leakage current	I_{GSS}	-	-	±100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	1.1	1.5	mΩ	VGS=10V, ID=95A
Transconductance	g_{fs}	117	233	467	S	V_{DS}=5V, I_D=95A
Dynamic Characteristic						
Input Capacitance	C_{iss}	8302	12453	18679	pF	V_{GS}=0V, V_{DS}=40V, f=1MHz
Output Capacitance	C_{oss}	1672	2508	3762		
Reverse Transfer Capacitance	C_{rss}	13	26	53		
Gate Total Charge	Q_G	114	172	257	nC	V_{GS}=10V, V_{DS}=50V, I_D=95A
Gate-Source charge	Q_{gs}	46	69	103		
Gate-Drain charge	Q_{gd}	9	18	37		
Turn-on delay time	$t_{d(on)}$	17	35	69	ns	V_{GS}=10V, V_{DD}=40V, R_{G_ext}=2.7Ω
Rise time	t_r	40	59	89		
Turn-off delay time	$t_{d(off)}$	66	99	149		
Fall time	t_f	27	41	62		
Gate resistance	R_G	0	1.8	8.99	Ω	V_{GS}=0V, V_{DS}=0V, f=1MHz

©China Resources Microelectronics (Chongqing) Limited

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.85	1.4	V	V_{GS}=0V,I_{SD}=95A
Body Diode Reverse Recovery Time	t_{rr}	58	116	232	ns	I_F=95A,dI/dt=100A/μs
Body Diode Reverse Recovery Charge	Q_{rr}	158	316	632	nC	

©China Resources Microelectronics (Chongqing) Limited

Typical Performance Characteristics

Fig 1: Output Characteristics

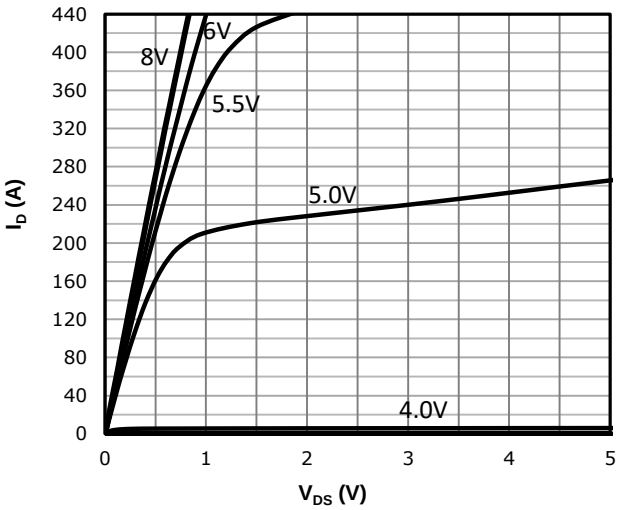


Fig 2: Transfer Characteristics

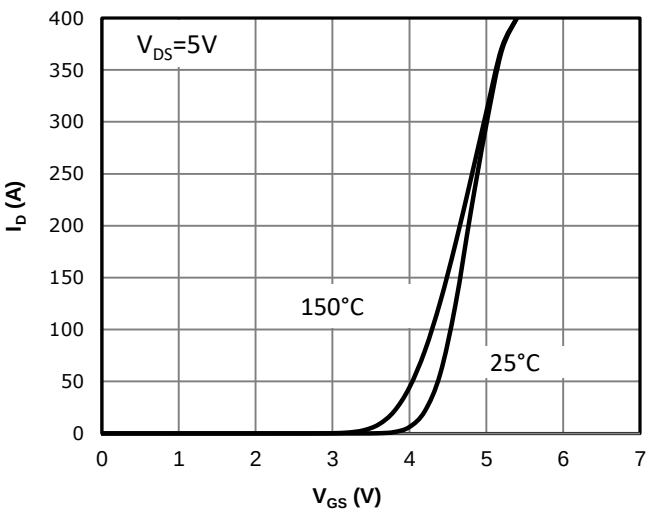


Fig 3: Rds(on) vs Drain Current and Gate Voltage

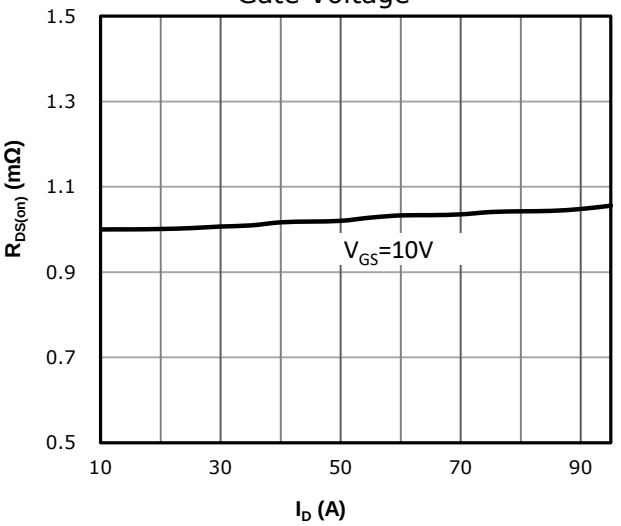


Fig 4: Rds(on) vs Gate Voltage

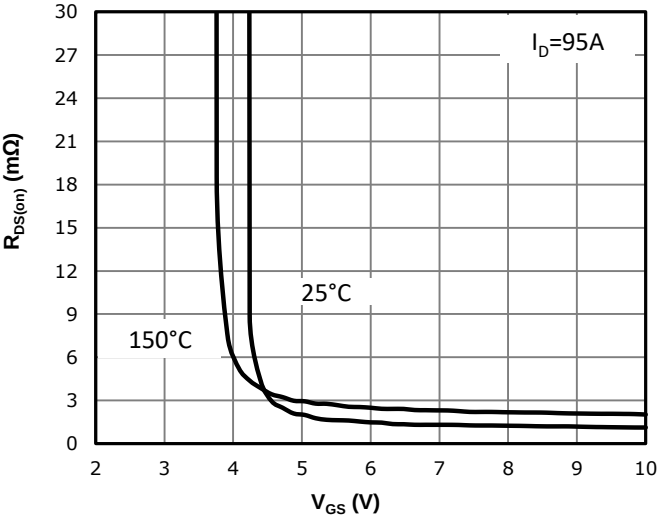


Fig 5: Rds(on) vs. Temperature

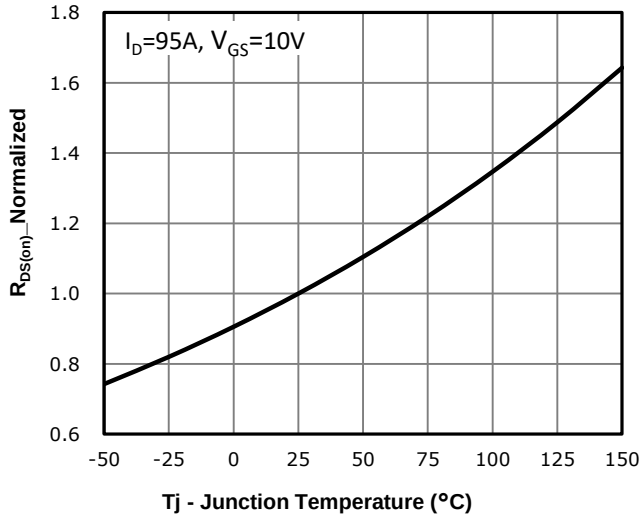
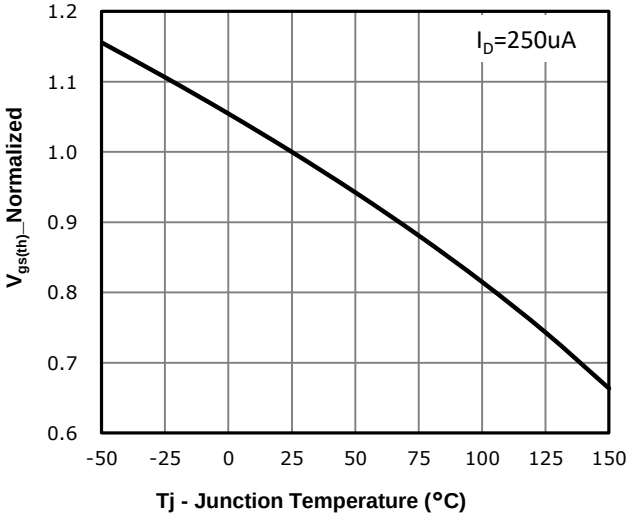


Fig 6: Vgs(th) vs. Temperature



©China Resources Microelectronics (Chongqing) Limited

Fig 7: BVdss vs. Temperature

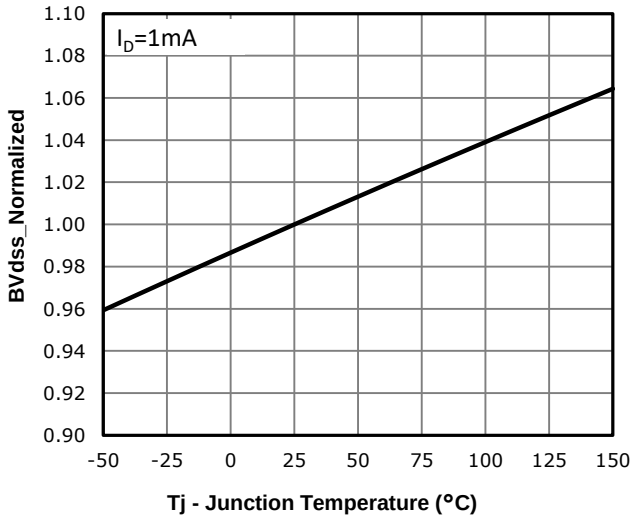


Fig 8: Capacitance Characteristics

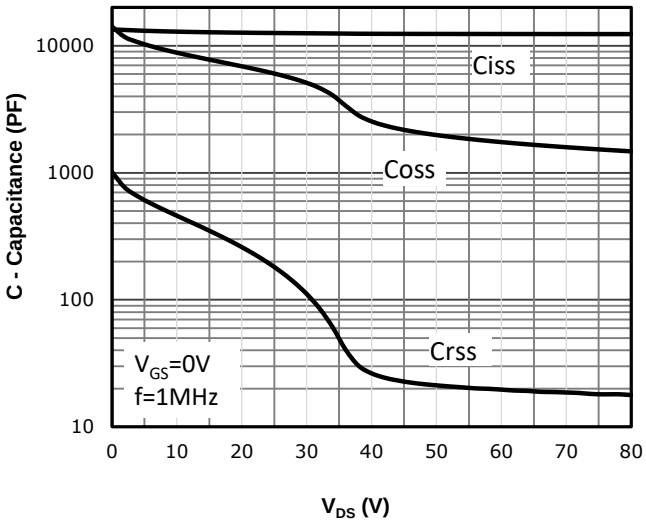


Fig 9: Gate Charge Characteristics

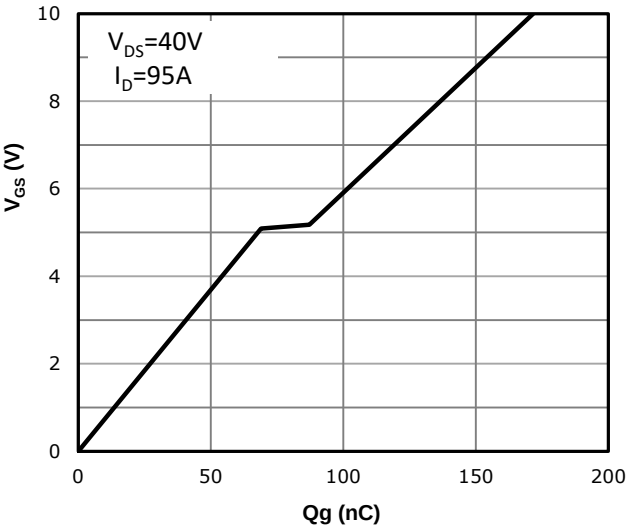


Fig 10: Body-diode Forward Characteristics

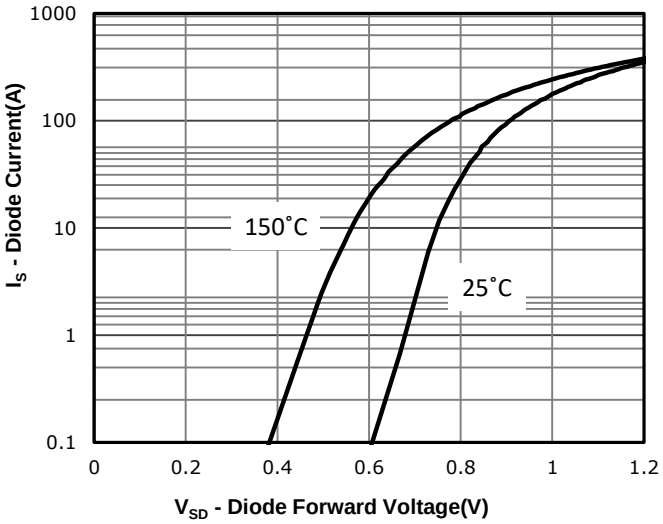


Fig 11: Power Dissipation

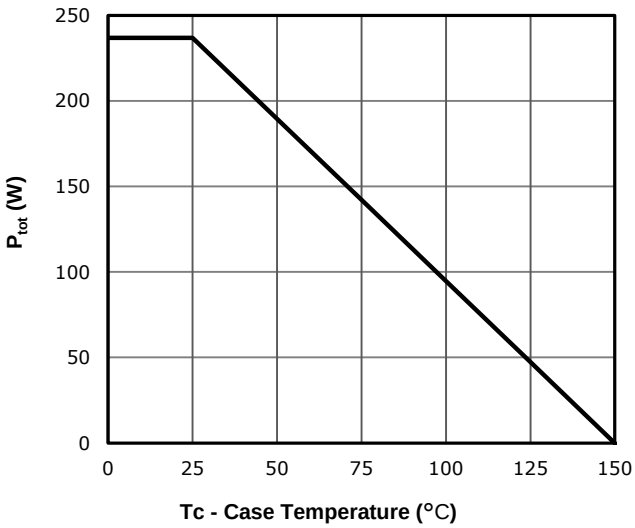
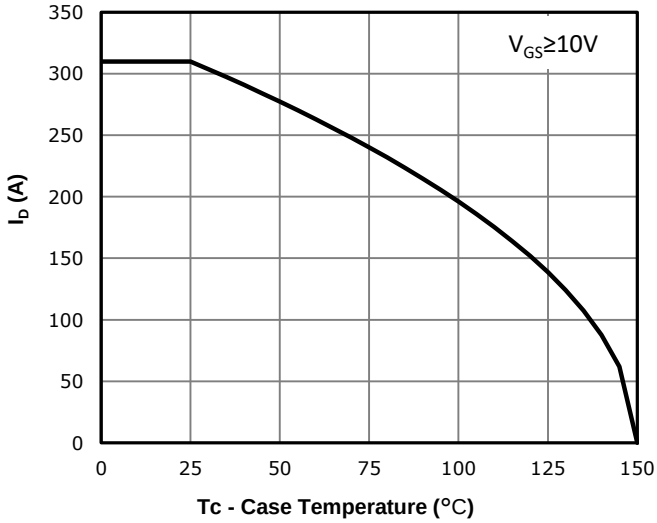


Fig 12: Drain Current Derating



©China Resources Microelectronics (Chongqing) Limited

Fig 13: Safe Operating Area

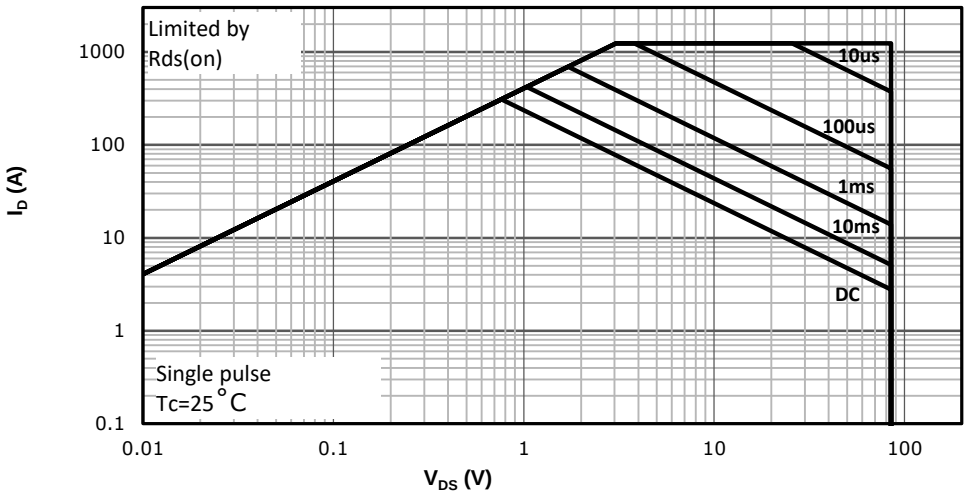
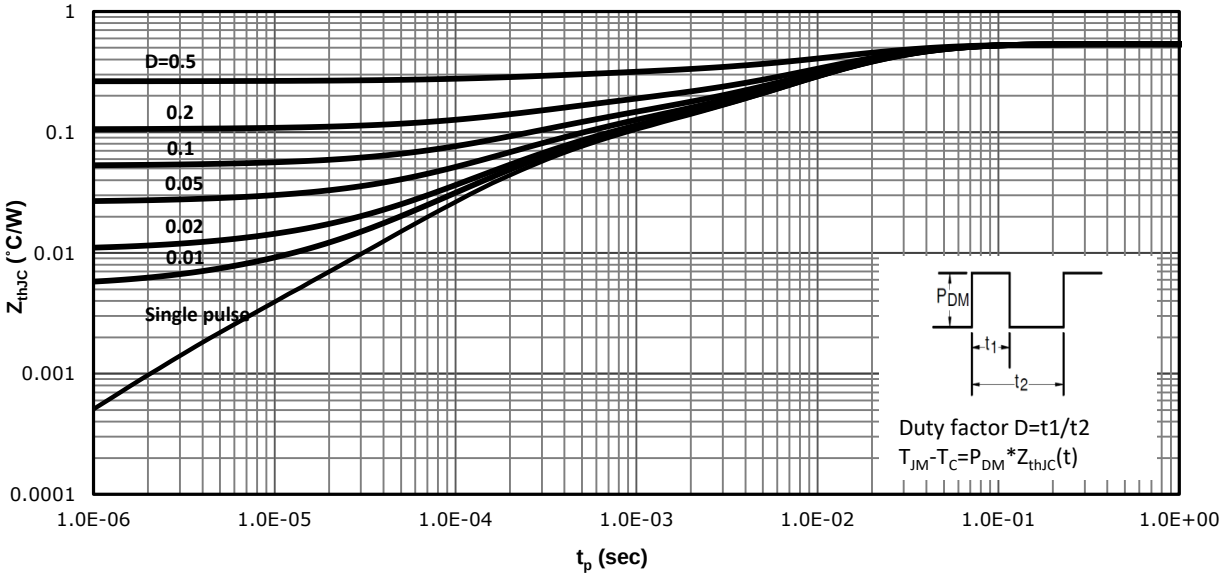


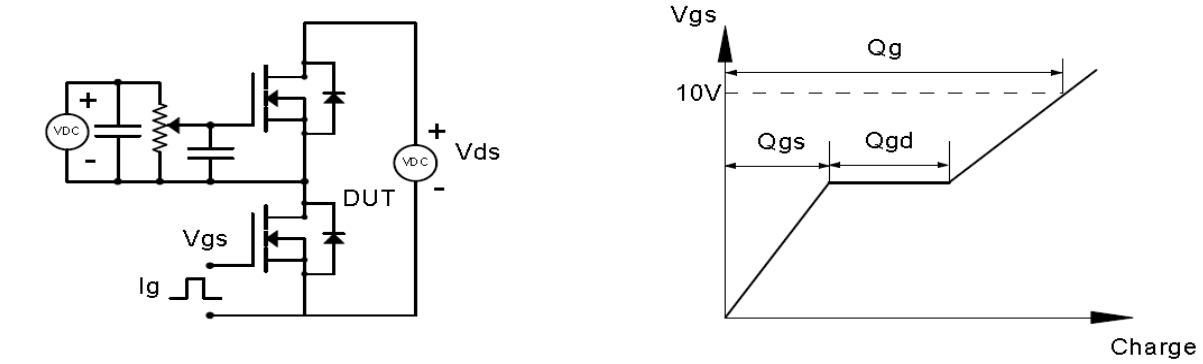
Fig 14: Max. Transient Thermal Impedance



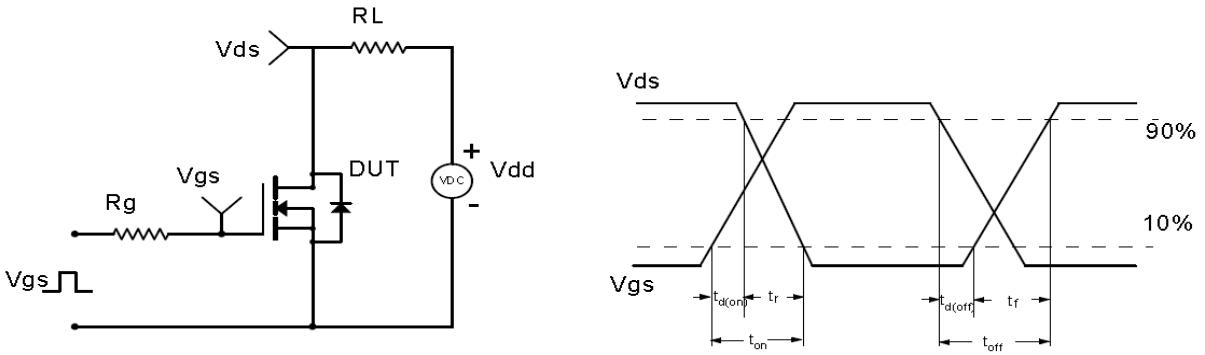
©China Resources Microelectronics (Chongqing) Limited

Test Circuit & Waveform

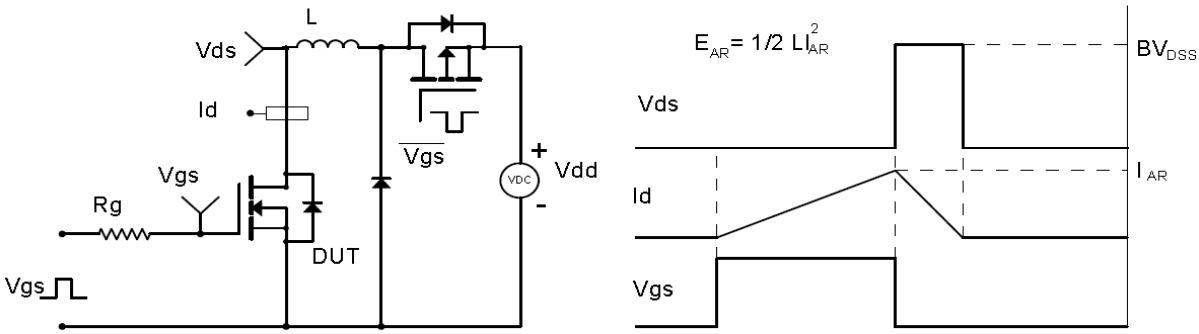
Gate Charge Test Circuit & Waveform



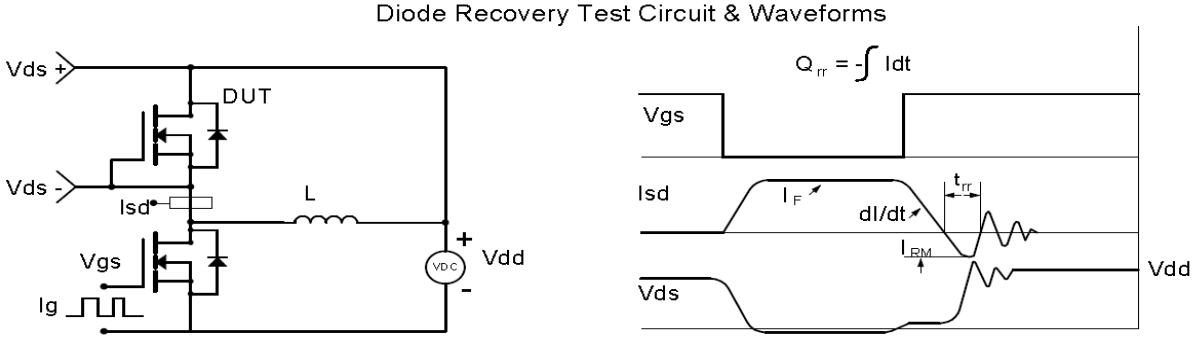
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

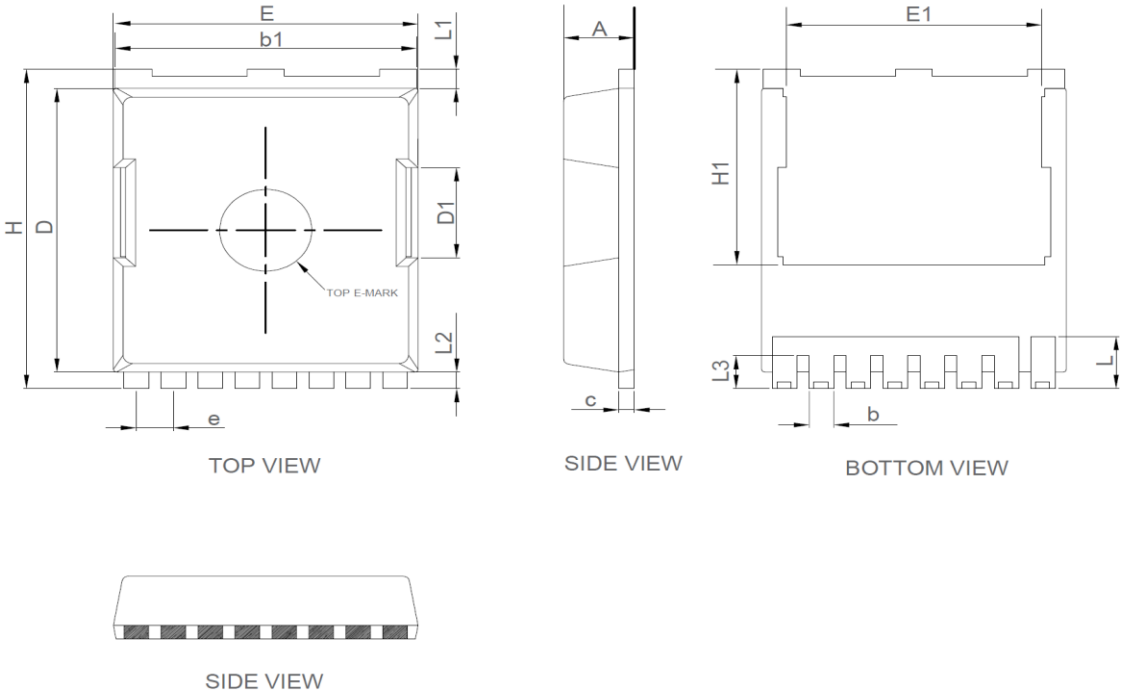


Diode Recovery Test Circuit & Waveforms



©China Resources Microelectronics (Chongqing) Limited

Package Outline: TOLL



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.15	2.45	0.085	0.096
b	0.60	0.90	0.024	0.035
b1	9.65	9.95	0.380	0.392
c	0.35	0.65	0.014	0.026
D	10.18	10.70	0.401	0.421
D1	3.15	3.45	0.124	0.136
E	9.70	10.10	0.382	0.398
E1	7.35	8.45	0.289	0.333
e	1.10	1.30	0.043	0.051
H	11.45	11.95	0.451	0.470
H1	6.55	7.50	0.258	0.295
L	1.35	2.10	0.053	0.083
L1	0.50	0.90	0.020	0.035
L2	0.40	0.80	0.016	0.031
L3	0.95	1.35	0.037	0.053

©China Resources Microelectronics (Chongqing) Limited

Marking



NOTE:
NXBBAAAAY

N	—Wire Bond code
X	—Assembly location code
BB	—Fab code
AAAA	—Lot code
Y	—Bin code

©China Resources Microelectronics (Chongqing) Limited

Revision History

Revision	Date	Major changes
1.0	2023/8/5	Release of Preliminary version.
1.1	2023/11/23	Update BVDSS/trr/Qrr.

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semicondutor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

©China Resources Microelectronics (Chongqing) Limited